

NOT RECOMMENDED FOR NEW DESIGN **USE DMN2056U**



DMN2075U

N-CHANNEL ENHANCEMENT MODE MOSFET

Features

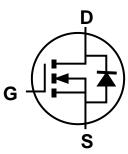
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

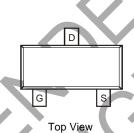
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)







Internal Schematic



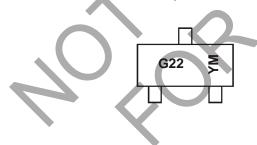
Ordering Information (Note 4)

			$\overline{}$	
Part Number		Case		Packaging
DMN2075U-7		SOT23		3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



G22 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Year	2009	,		2017	2018	2019	2020	2021	202	22 2	023	2024	2025
Code	W	,		Е	F	G	Н	1	J		K	L	М
Mont	h	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	е	1	2	3	4	5	6	7	8	9	0	N	D



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Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characte	eristic		Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±8	V	
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +70°C	I _D	4.2 3.4	А
Maximum Continuous Body Diode For	ote 6)	Is	1.2	Α	
Pulsed Drain Current (Note 6)			I _{DM}	27	Α
Pulsed Body Diode Forward Current (N	Note 6)		I _{SM}	24	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	0.8	W
Thermal Resistance, Junction to Ambient @T _A = +25°C	$R_{\theta JA}$	156	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by junction temperature.

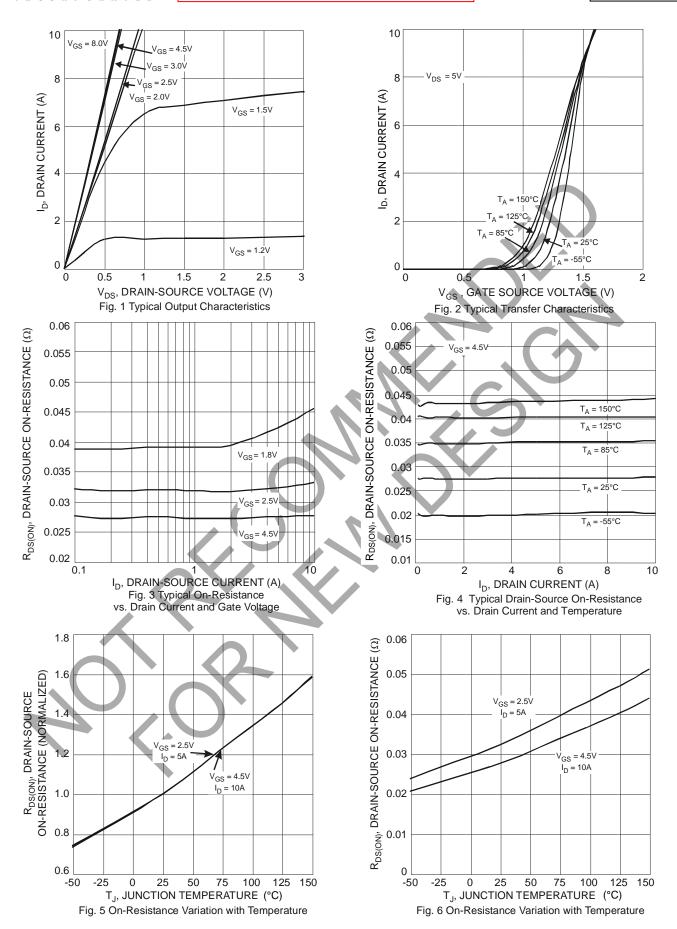
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			1			
Drain-Source Breakdown Voltage	BV _{DSS}	20	_		V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}			100	nA	$V_{DS} = 16V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_		±100	nA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.4		1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	Dragan		25	38	mΩ	$V_{GS} = 4.5V, I_D = 3.6A$
Static Drain-Source Off-Resistance	R _{DS(ON)}		30	45		$V_{GS} = 2.5V, I_D = 3.1A$
Forward Transfer Admittance	Y _{FS}	_	13	_	S	$V_{DS} = 5V, I_{D} = 3.6A$
Diode Forward Voltage	V_{SD}	1	0.75	1.0	V	$V_{GS} = 0V$, $I_S = 1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	, —	594.3	_	pF	101/1/
Output Capacitance	Coss	_	64.5		pF	$V_{DS} = 10V, V_{GS} = 0V,$ $V_{DS} = 100$
Reverse Transfer Capacitance	C _{RSS}	_	57.7	_	pF	1 = 1.01/11/12
Gate Resistance	R_g	_	1.5		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Q_{G}	_	7.0	_	nC	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
Gate-Source Charge	Q _{GS}	_	0.9	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$
Gate-Drain Charge	Q_GD	_	1.4	_	nC	$I_D = 3.6A$
Turn-On Delay Time	t _{D(ON)}	_	7.4	_	ns	
Turn-On Rise Time	t _R	_	9.8	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	28.1	_	ns	$R_L = 2.78\Omega, R_g = 1.0\Omega$
Turn-Off Fall Time	t _F	_	6.7	_	ns	

Notes:

- 7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to production testing.





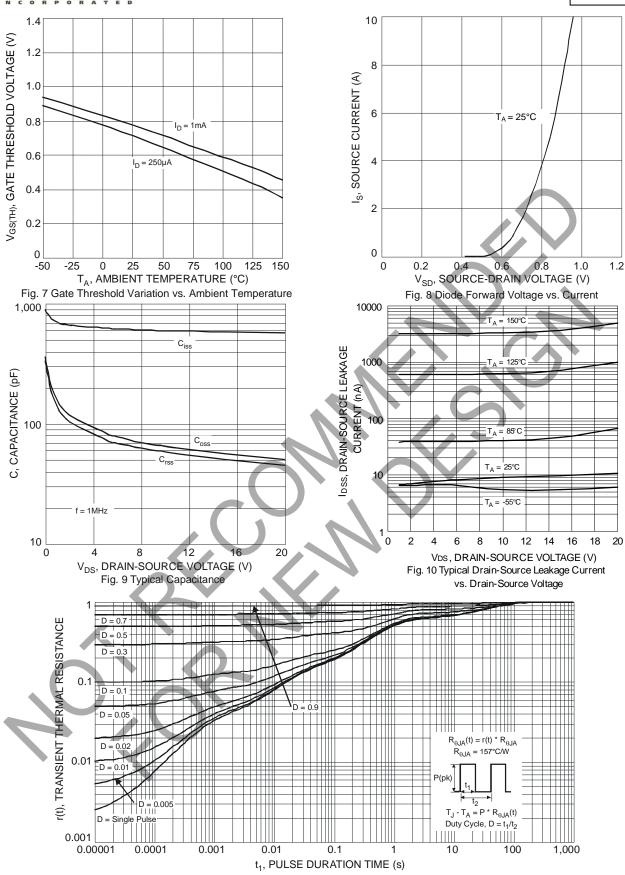
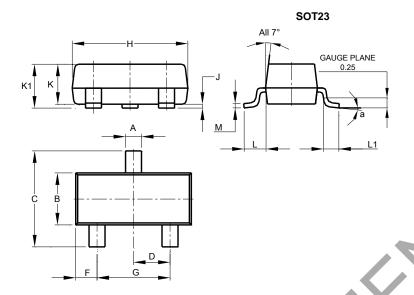


Fig. 11 Transient Thermal Response



Package Outline Dimensions

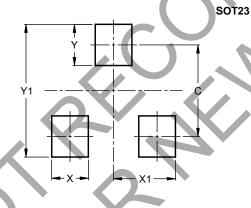
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°	- -				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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